

# New Jersey Semi-Conductor Products, Inc.

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2N6137

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## ABSOLUTE MAXIMUM RATINGS

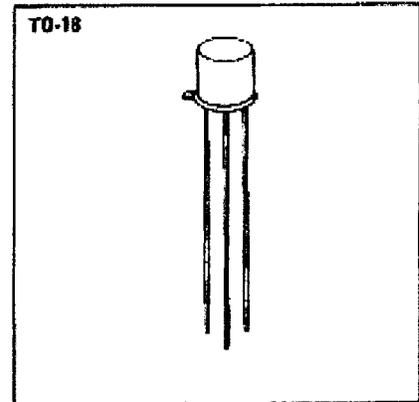
Anode-to-Cathode Forward Voltage, $V_{AK}$	40V
Anode-to-Cathode Reverse Voltage, $V_{AKR}$	40V
Gate-to-Cathode Forward Voltage, $V_{GK}$	40V
Gate-to-Anode Reverse Voltage, $V_{GAR}$	40V
Gate-to-Cathode Reverse Voltage, $V_{GKR}$	5V
Peak Recurrent Forward Current, $10\mu s$ 1% Duty Cycle	5A
Peak Gate Current, $I_{GM}$	250mA
Average Gate Current, $I_{G(AV)}$	50mA
Power Dissipation	
25°C Ambient	300mW
Derating Factor	2.4mW/°C
Storage Temperature Range	-55°C to +125°C
Operating Temperature Range	-55°C to +125°C

## MECHANICAL SPECIFICATIONS

GATE CONNECTED TO CASE

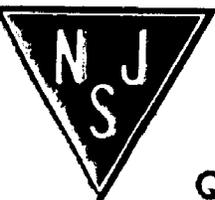
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	INCHES	MILLIMETERS
A	178-189 DIA	4.52-4.80 DIA
B	170-219	4.31-5.51
C	3 MIN	12.70 MIN
D	209-230 CW	5.31-5.84 DIA
E	0.17 ± 0.02 DIA 0.01 DIA	4.32 ± 0.25 0.25
F	620 MAX	508 MAX
G	300 ± 0.10 DIA	2.54 ± 0.254 DIA.
H	0.41 ± 0.05	1.04 ± 1.27
J	0.28-0.48	7.11-1.22



## ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Test	Symbol	Figure	Minimum	Typical	Maximum	Units	Test Conditions
<b>SUBGROUP 1 Visual and Mechanical</b>							
<b>SUBGROUP 2</b>							
Gate-anode blocking current	$I_{GAD}$	2	—	2	10	nA	$V_{GA} = \text{Rating}$
Gate-cathode blocking current	$I_{GKS}$	3	—	5	100	nA	$V_{GC} = \text{Rating}$
<b>SUBGROUP 3</b>							
Peak-point anode current	$I_p$	1	—	1 2.5	2 5	$\mu A$ $\mu A$	$R_g = 1 \text{ Meg}$ $R_g = 10K$ } $V_s = 10V$
Peak-point offset voltage	$V_T$	1	0.2 0.2	0.26 0.35	1.6 0.6	V V	$R_g = 1 \text{ Meg}$ $R_g = 10K$ } $V_s = 10V$
Valley-point anode current	$I_V$	1	— 70 1.5	15 200 2	50 — —	$\mu A$ $\mu A$ mA	$R_g = 1 \text{ Meg}$ $R_g = 10K$ $R_g = 200\Omega$ } $V_s = 10V$
<b>SUBGROUP 4</b>							
Forward on-state voltage	$V_F$	4	—	0.85	1.0	V	$I_s = 50mA$
Peak pulse voltage	$V_o$	5	9	12	—	V	
Peak pulse voltage rise time	$t_r$	5	—	50	80	ns	
<b>SUBGROUP 5</b>							
Gate-anode blocking current (125°C Test)	$I_{GAD}$	2	—	150	500	nA	$V_{GA} = \text{Rating}$
Valley-point anode current (125°C Test)	$I_V$	1	40	100	—	$\mu A$	$R_g = 10K, V_s = 10V$
Peak-point anode current (-55°C Test)	$I_p$	1	—	7.5	10	$\mu A$	$R_g = 10K, V_s = 10V$



Quality Semi-Conductors